



4-BIT BI-DIRECTIONAL LEVEL TRANSLATOR OPEN-DRAIN AND PUSH-PULL APPLICATIONS

Description

The LSF0204 is a 4-channel bi-directional multi-voltage level translator for open-drain and push-pull applications. This device is a universal level translator with A port operating from 0.8V to 4.5V (Vref_A) and B port from 1.8V to 5.5V (Vref_B). This range allows for bi-directional voltage translations between 0.8V and 5.0V. Be aware that Vref_B is recommended to be at 1.0V higher than Vref_A for the best signal integrity.

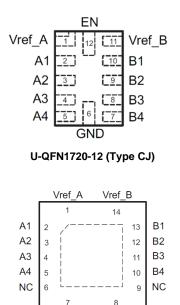
The EN pin is used to activate the device. When EN is HIGH, the translator switch is on. Otherwise, if EN is LOW, the translator switch is off, and a high-impedance state exists between ports. The EN input circuit is designed to be supplied by Vref_A. EN must be LOW to ensure the high-impedance state during power-up or power-down to avoid misoperation.

Please note that an external Rpu (pullup resistor) is required on port A and B for push-pull and open-drain application because a pull-high state can avoid misoperation during the power sequence. About the Rpu, the smaller value can result in the larger driving current. Overall, the LSF0204 is designed for easy-to-use with auto direction. So, there is no need for a direction pin to minimize system effort. This device supports 5V tolerant I/O pins for compatibility with TTL levels in a variety of applications which require a proper voltage translation.

Features

- External Rpu (Pullup Resistor) to Set Driving Current in Both Push-Pull and Open-Drain Applications
- Up & Down Translation
 - \leq 100MHz; C_L = 15pF, 30pF
 - \leq 50MHz; C_L = 50pF
- Bi-Directional Voltage Level Translation Between:
 - 0.8V and 1.8V, 2.5V, 3.3V and 5.0V
 - 1.2V and 1.8V, 2.5V, 3.3V and 5.0V
 - 1.8V and 2.5V, 3.3V and 5.0V
 - 2.5V and 3.3V and 5.0V
 - 3.3V and 5.0V
- ESD Protection Exceeds JESD 22
 - 2000V HBM (A114)
 - 1000V CDM (C101)
- Latchup Exceeds 100mA per JESD 17
- Specified from -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (<u>LSF0204Q</u>)

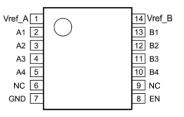
Pin Assignments



V-QFN3535-14 (Type CJ)

FN

GND



TSSOP-14

Applications

- GPIO, MDIO, SDIO, SVID, UART
- PMBus™, SMBus™, I2C, and other interfaces
- Telecom infrastructures
- Industrial
- High-performance computing
- Wide array of products such as:
 - PCs, networking, notebooks
 - Smart phones
 - Tablets

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Pin Descriptions

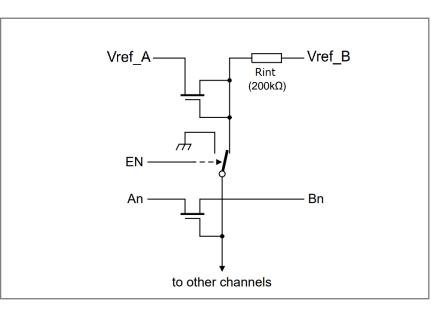
Pin Name	TSSOP-14	U-QFN1720-12 (Type CJ)	V-QFN3535-14 (Type CJ)	Function
V _{ref_} A	1	1	1	Reference supply voltage; A port
A1	2	2	2	Input/output 1
A2	3	3	3	Input/output 2
A3	4	4	4	Input/output 3
A4	5	5	5	Input/output 4
NC	6	—	6	No connection. Not internally connected.
GND	7	6	7	Ground
EN	8	12	8	Switch enable input; EN is high-active.
NC	9	—	9	No connection. Not internally connected.
B4	10	7	10	Input/output 4
B3	11	8	11	Input/output 3
B2	12	9	12	Input/output 2
B1	13	10	13	Input/output 1
V _{ref_B}	14	11	14	Reference supply voltage; B port

Absolute Maximum Ratings (Note 4)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	±2	kV
ESD CDM	Charged Device Model ESD Protection	±1	kV
VREF	Supply Reference Voltage Range	-0.5 to +6.0	V
VI	Input Voltage Range	-0.5 to +6.0	V
Vo	Voltage Range Applied to Any Output in the High-Z or Power-Off State	-0.5 to +6.0	V
Існ	Continuous Channel Current	128	mA
Ік	Input Clamp Current, VI < 0	-50	mA
TJ	Operating Junction Temperature	-40 to +150	۵°
Tstg	Storage Temperature	-65 to +150	°C

Note: 4. Stresses greater than those listed under Absolute Maximum Ratings can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to Absolute Maximum Ratings for extended periods can affect device reliability.

Functional Diagram





Recommended Operating Conditions (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V _{REF}	Reference Voltage, A & B Ports	0.8	5.5	V
VI/O	Input/Output Voltage	0.8	5.5	V
VEN	Enable Voltage	0	5.5	V
IPASS	Pass Transistor Current	—	64	mA
T _A	Operating Free-Air Temperature	-40	+125	°C

Electrical Characteristics (Note 5) (@TA = +40°C to +125°C, unless otherwise specified.)

Symbol	Parameter	Т	est Conditions	Min	Тур	Max	Unit
V _{ref_A}	A Port Supply Voltage	_		0.8	_	4.5	V
V _{ref_B}	B Port Supply Voltage	—		1.8	_	5.5	V
V _{IK}	—	$I_I = -18mA, V_{EN} = 0$		-1.2	_	_	V
I _{IH}	—	$V_{I} = 5V, V_{EN} = 0$		_	_	5.0	μA
I _{CCBA}	Leakage from Vref B to Vref_A	$V_{ref_B} = 3.3V, V_{ref_A} = V_1 = 3.3V$ or GND	= 1.8V, $V_{EN} = V_{ref_A}$, $I_O = 0$	—	_	3.5	μA
I _{CCA} + I _{CCB}	Total Current Through GND	$V_{ref_B} = 3.3V, V_{ref_A} = V_I = 3.3V \text{ or } GND$	= 1.8V, $V_{EN} = V_{ref_A}$, $I_O = 0$	—	0.2	_	μA
I _{IN}	Control Pin Current	Vref_B = 5.5V, Vref_A	= 4.5V, V_{EN} = 0 to V_{ref_A} , I_O = 0	—	—	±1	μA
I _{off}	Power Off Leakage Current	$V_{ref_B} = V_{ref_A} = 0, V_E$	$E_N = GND, I_O = 0, V_I = 5V \text{ or } GND$	—	_	±1	μA
$C_{\text{I}}(\text{ref}_\text{A/B/EN})$	—	$V_I = 3V \text{ or } 0$		—	7	—	pF
C _{io (off)}	—	$V_0 = 3V \text{ or } 0, V_{EN} =$	0	—	5.0	6.0	pF
C _{io (on)}	—	$V_{O} = 3V \text{ or } 0, V_{EN} =$	V _{ref_A}	—	10.5	13	pF
V _{IH (EN)}	High-Level Input Voltage	V _{ref_A} = 1.5V to 4.5V	1	0.7×V _{ref_A}	_	_	V
V _{IL (EN)}	Low-Level Input Voltage	V _{ref_A} = 1.5V to 4.5V	1	_	_	0.3×Vref_A	V
V _{IH} (EN)	High-Level Input Voltage	V _{ref_A} = 1.0V to 1.5V	0.8×V _{ref_A}	_	_	V	
V _{IL} (EN)	Low-Level Input Voltage	V _{ref_A} = 1.0V to 1.5V	1	_	_	0.3×Vref_A	V
$\Delta t/\Delta v$ (EN)	Input Transition Rise or Fall Rate for EN Pin	_		—	10	_	ns/V
		V/- 0 lo 64mA	$V_{ref_A} = V_{EN} = 3.3V$; $V_{ref_B} = 5V$	—	3	—	Ω
		$V_1 = 0, 10 = 6411A$	$V_{ref_A} = V_{EN} = 1.8V$; $V_{ref_B} = 5V$	—	4	—	12
		V/- 0 Iz 20mA	$V_{ref_A} = V_{EN} = 1.0V$; $V_{ref_B} = 5V$	—	5	_	Ω
		VI = 0, IO = 32 mA	$V_{ref_A} = V_{EN} = 1.8V$; $V_{ref_B} = 5V$	—	4	—	12
R _{on}		VI = 0, Io = 32mA, Vr	$ef_A = V_{EN} = 2.5V; V_{ref_B} = 5V$	—	3	_	Ω
Non	_	$V_{I} = 0, I_{O} = 64mA$ $V_{ref_{A}} = V_{EN} = 1.8V; V_{ref_{B}} = 5V$ $V_{I} = 0, I_{O} = 32mA$ $V_{ref_{A}} = V_{EN} = 1.0V; V_{ref_{B}} = 5V$		—	5	_	Ω
		$V_{I} = 1.0V, I_{O} = 10m$ $V_{ref_{B}} = 3.3V$	A, $V_{ref_A} = V_{EN} = 1.8V$	_	8	_	Ω
		$V_{I} = 0, I_{O} = 10 m A, V_{O}$	/ref_A = VEN = 1.0V; Vref_B = 3.3V	—	6	—	Ω
		$V_{I} = 0$, $I_{O} = 10 \text{mA}$, $V_{I} = 0$	Vref_A = VEN = 1.0V; Vref_B = 1.8V	_	6	_	Ω

Note: 5. All typical values are at T_A = +25°C. Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) terminals. The actual supply current for LSF0204 is I_{CCA} + I_{CCB}; the leakage from Vref_B to Vref_A can be measured on Vref_A and Vref_B pins.



EN Pin Characteristics (Note 6) (@TA = +40°C to +125°C, unless otherwise specified.)

Translating Down, 3.3V to 1.8V

Parameter			CL =	C∟ = 50pF		C∟ = 30pF		C∟ = 15pF	
Parameter			Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLZ} (LOW to OFF)	From EN Pin	To Port A or B	13	20	12	20	11	20	ns
t _{PZL} (OFF to LOW)			35	50	30	40	25	40	ns
Test Conditions: Vr otherwise noted, s		= 3.3V, V _M = 0.9V, V	′εν = 1.8V, V	'EXT = Vref_A,	Rpu = NA, V	ін = 3.3V, VIL	= 0, PRR =	10MHz (unle	SS

Translating Up, 1.8V to 3.3V

Parameter			CL =	50pF	CL =	30pF	CL =	15pF	Unit
Parameter			Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLZ} (LOW to OFF)	From EN Pin	To Port A or B	13	20	12	20	11	20	ns
t _{PZL} (OFF to LOW)			35	50	30	40	25	40	ns
Test Conditions: Vr otherwise noted, s	_{ef_A} = 1.8V, V _{ref_B} = see Figure 1)	: 3.3V, V _M = 0.9V, V	′ _{EN} = 1.8V, V	'EXT = Vref_A,	Rpu = NA, V	′ін = 3.3V, Vil	= 0, PRR =	10MHz (unle	SS

Translating Down Characteristics (Note 6) (@T_A = +40°C to +125°C, unless otherwise specified.)

Translating Down, 5.0V to 1.8V

Parameter	From (Input)	To (Output)	C∟ = 50pF		C∟ = 30pF		C∟ = 15pF		Unit	
Parameter	From (input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit	
t _{PLH}			0.6	5.1	0.5	5.1	0.3	5.0	ns	
t _{PHL}	В	А	1.1	4.8	0.9	4.5	0.5	4.4	ns	
f _{MAX}			5	50	1	00	1	00	MHz	

Translating Down, 3.3V to 1.8V

Parameter			CL =	50pF	CL =	30pF	CL =	15pF	Unit
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH}			0.7	5.5	0.5	5.3	0.3	5.2	ns
t _{PHL}	В	А	0.9	4.9	0.7	4.7	0.5	4.5	ns
f _{MAX}			Ę	50	1	00	1	00	MHz
Test Conditions: V see Figure 1)	ref_A = 1.8V, V _{ref_B} =	: 3.3V, V _M = 1.15V,	V _{EN} = 1.8V,	Switch = S2,	V _{IH} = 3.3V,	V _{IL} = 0, PRR	= 10MHz (ur	nless otherwi	se noted,

Translating Down, 3.3V to 1.2V

Parameter	From (Innut)		CL =	50pF	CL =	30pF	CL =	15pF	Unit
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH}			0.8	4.1	0.5	3.9	0.3	3.8	ns
t _{PHL}	В	А	0.9	4.7	0.7	4.5	0.6	4.3	ns
f _{MAX}			5	50	1	00	1	00	MHz
Test Conditions: Vr see Figure 1)	ref_A = 1.2V, Vref_B =	: 3.3V, V _M = 0.85V,	$V_{EN} = 1.2V,$	Switch = S2,	VIH = 3.3V,	VIL = 0, PRR	= 10MHz (u	nless otherwi	se noted,

Note: 6. All typical values are measured at T_A = +25°C. Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10MHz; Z_O = 50Ω. Definitions test circuit: C_L = Load capacitance including jig and probe capacitance; Rpu = pullup resistor as load resistance; S1/S2 = Test selection switch.



Translating Down Characteristics (continued) (Note 6) (@TA = +40°C to +125°C, unless otherwise specified.)

Translating Down, 1.8V to 1.2V

Deremeter			C∟ = 50pF		C∟ = 30pF		C∟ = 15pF		l Init
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH}			1.3	4.6	1.1	4.4	1.0	4.1	ns
t _{PHL}	В	А	1.4	5.3	1.3	5.1	1.2	4.7	ns
f _{MAX}			Ę	50	1	00	1	00	MHz
Test Conditions: V ₁ see Figure 1)	ref_A = 1.2V, Vref_B =	: 1.8V, V _M = 0.65V,	V _{EN} = 1.2V,	Switch = S2,	VIH = 1.8V,	VIL = 0, PRR	= 10MHz (ur	nless otherwi	se noted,

Translating Down, 1.8V to 0.8V

Parameter	From (Innut)		CL =	C∟ = 50pF		C _L = 30pF		C _L = 15pF		
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit	
t _{PLH}			1.5	4.7	1.2	4.5	1.1	4.3	ns	
t _{PHL}	В	А	1.7	5.6	1.6	5.3	1.3	5.0	ns	
f _{MAX}			Ę	50	8	30	1	00	MHz	
Test Conditions: Vr see Figure 1)	$r_{ef_A} = 0.8V, V_{ref_B} =$	50 80 100 .8V, V _{ref_B} = 1.8V, V _M = 0.55V, V _{EN} = 0.8V, Switch = S2, V _{IH} = 1.8V, V _{IL} = 0, PRR = 10MHz (unless otherwise								

Translating Up Characteristics (Note 6) (@T_A = +40°C to +125°C, unless otherwise specified.)

Translating Up, 1.8V to 5.0V

Deremeter			C _L =	C∟ = 50pF		30pF	C _L =	15pF	Unit
Parameter	From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH}			0.6	5.7	0.4	5.3	0.2	5.2	ns
t _{PHL}	A	В	1.3	6.7	1.0	6.4	0.7	5.3	ns
f _{MAX}			Ę	50	1	00	1	00	MHz
	ref_A = 1.8V, Vref_B = noted, see Figure		$V_{EN} = 1.8V,$	Switch = S1,	Rpu = 5000	$V_{EXT} = 5.0V$	/, V _{IH} = 1.8V	$V_{IL} = 0$, PRF	R = 10MHz

Translating Up, 1.8V to 3.3V

Decemptor From (Input)			CL =	50pF	CL =	30pF	CL =	15pF	Unit
Parameter From (Input)	To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit	
t _{PLH}			0.6	5.7	0.4	5.3	0.2	5.2	ns
t _{PHL}	A	В	1.3	6.7	1.0	6.4	0.7	5.3	ns
f _{MAX}			5	50	1	00	1	00	MHz
	Imax 50 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 1000 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 100 </td								

Translating Up, 1.2V to 3.3V

Desemator		rom (Input) To (Output) T	CL =	50pF	CL =	30pF	CL =	15pF	l lmit
Parameter	neter From (input)		Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH}			0.7	7.3	0.4	7.1	0.2	6.9	ns
t _{PHL}	A	В	1.6	7.1	1.3	6.5	1.0	5.4	ns
f _{MAX}			Ę	50	1	00	1	00	MHz
	$_{ref_A} = 1.2V, V_{ref_B} = 0$ noted, see Figure 2		V _{EN} = 1.2V,	Switch = S1,	Rpu = 5000	Ω, VEXT = 3.3V	/, Viн = 1.2V	, Vı∟ = 0, PRF	R = 10MHz

Note: 6. All typical values are measured at T_A = +25°C. Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10MHz; Z_O = 50Ω. Definitions test circuit: C_L = Load capacitance including jig and probe capacitance; Rpu = pullup resistor as load resistance; S1/S2 = Test selection switch.



Translating Up Characteristics (continued) (Note 6) (@TA = +40°C to +125°C, unless otherwise specified.)

Translating Up, 1.2V to 1.8V

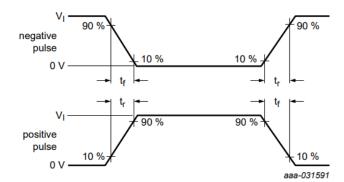
Deremeter	Parameter From (Input)	To (Output)	CL = 50pF		CL = 30pF		C∟ = 15pF		Unit
Parameter			Тур	Max	Тур	Max	Тур	Max	Onic
t _{PLH}			0.7	7.3	0.4	7.1	0.2	6.9	ns
t _{PHL}	А	В	1.6	7.1	1.3	6.5	1.0	5.4	ns
f _{MAX}			Ę	50	1	00	1	00	MHz
	$\frac{V_{MAX}}{V_{MAX}} = \frac{100}{100} = \frac{100}$								

Translating Up, 0.8V to 1.8V

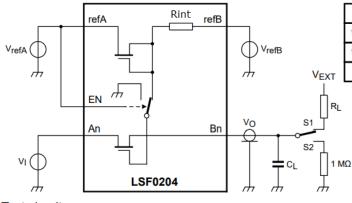
Parameter		To (Output)	C _L =	50pF	C _L =	30pF	C _L =	15pF	Unit
Parameter	From (Input) To (To (Output)	Тур	Max	Тур	Max	Тур	Max	Unit
t _{PLH}			0.7	7.3	0.5	7.2	0.3	6.9	ns
t _{PHL}	А	В	1.6	7.1	1.4	6.6	1.0	5.4	ns
f _{MAX}			2	10	8	30	1	00	MHz
	ref_A = 0.8V, Vref_B = noted, see Figure		$V_{EN} = 0.8V,$	Switch = S1,	Rpu = 500Ω	, V _{EXT} = 1.8∖	/, V _{IH} = 0.8V	, V _{IL} = 0, PRF	R = 10MHz

Note: 6. All typical values are measured at T_A = +25°C. Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10MHz; Z_O = 50Ω. Definitions test circuit: C_L = Load capacitance including jig and probe capacitance; Rpu = pullup resistor as load resistance; S1/S2 = Test selection switch.

Parameter Measurement Information



V_I source waveform



Test circuit

switch

S1

S2

S1

Measurement

tPHL/tPLH, fmax

tPHL/tPLH, fmax

t_{PZL}/t_{PLZ}

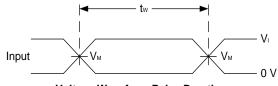
Translating up

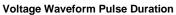
Translating down

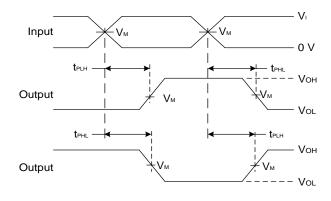
Translating up/down



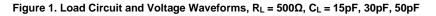
Parameter Measurement Information (continued)







Voltage Waveform Propagation Delay Times Inverting and Non-Inverting Outputs



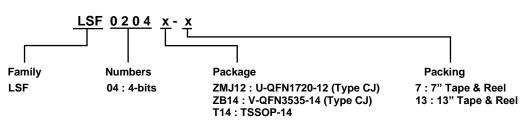
Package Characteristics

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
	Thermal Resistance Junction-to-Ambient	U-QFN1720-12 (Type CJ)		_	185	—	
θ_{JA}		TSSOP-14	(Note 7)	_	125	_	
		V-QFN3535-14 (Type CJ)		_	89	_	°C/W
		U-QFN1720-12 (Type CJ)		_	65	_	-C/W
Өлс	Thermal Resistance Junction-to-Case	TSSOP-14	(Note 7)	_	72	_	
		V-QFN3535-14 (Type CJ)		_	34	_	

Note: 7. Test condition for the package type(s): device mounted on JEDEC standard PCB per JESD51, with minimum recommended pad layout.



Ordering Information (Notes 8 & 9)



Part Number Part Number Suffix		Daakaga Cada	Deekere	Packing (Note 10)		
Part Number	Part Number Sumx	Package Code	Package	Qty.	Carrier	
LSF0204ZMJ12-7	-7	ZMJ12	U-QFN1720-12 (Type CJ)	3,000	7" Tape and Reel	
LSF0204ZB14-13	-13	ZB14	V-QFN3535-14 (Type CJ)	5,000	13" Tape and Reel	
LSF0204T14-13	-13	T14	TSSOP-14	2,500	13" Tape and Reel	

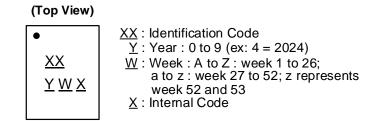
Notes: 8. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

9. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/packageoutlines.html.

10. The taping orientation is located on our website at https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf.

Marking Information

(1) U-QFN1720-12 (Type CJ)



Part Number	Package	Identification Code
LSF0204ZMJ12-7	U-QFN1720-12 (Type CJ)	J2

(2) V-QFN3535-14 (Type CJ)

(Top View)

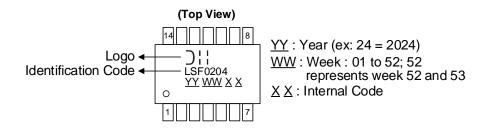
• <u>XX</u> YWX	$\frac{XX}{Y} : \text{Identification Code}$ $\frac{Y}{Y} : \text{Year} : 0 \text{ to } 9 \text{ (ex: } 4 = 2024\text{)}$ $\frac{W}{Y} : \text{Week} : A \text{ to } Z : \text{week } 1 \text{ to } 26\text{;}$ $a \text{ to } z : \text{week } 27 \text{ to } 52\text{; } z \text{ represents}$ $\text{week } 52 \text{ and } 53$
	<u>X</u> : Internal Code

Part Number	Package	Identification Code		
LSF0204ZB14-13	V-QFN3535-14 (Type CJ)	JE		



Marking Information (continued)

(3) TSSOP-14



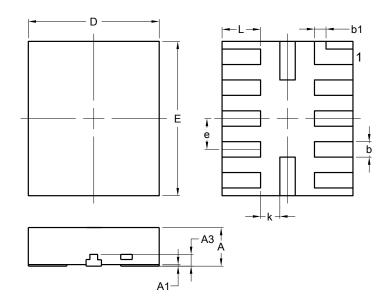
Part Number	Package	Identification Code
LSF0204T14-13	TSSOP-14	LSF0204



Package Outline Dimensions

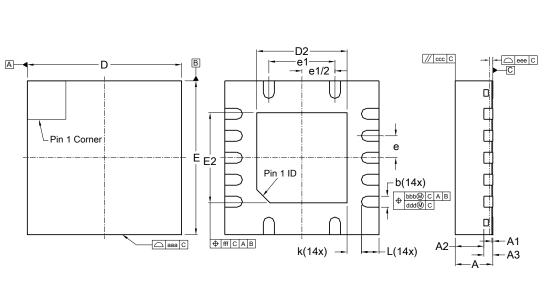
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) U-QFN1720-12 (Type CJ)



	U-QFN1720-12 (Type CJ)						
Dim	Min	Max	Тур				
Α	0.450	0.550					
A1	0.00	0.050					
A3	0	.152 RE	F				
b	0.150	0.250	-				
b1	0	.150 RE	F				
D	1.600	1.800	-				
E	1.900	2.100	-				
е	0	.400 BS	iC				
k	0	.250 RE	F				
L	0.400	0.600					
All [Dimens	ions in	mm				

(2) V-QFN3535-14 (Type CJ)



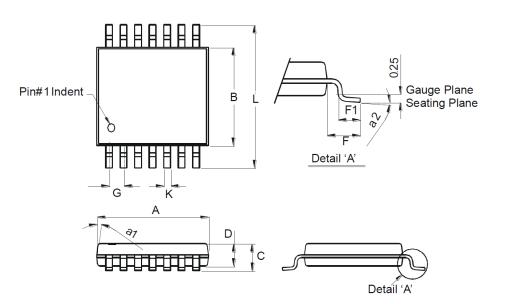
	V-QFN	3535-1	4						
	(Type CJ)								
Dim	Min	Max	Тур						
Α	0.80	0.90	0.85						
A1	0.00	0.05	0.02						
A2			0.65						
A3	0	.203 R	EF						
b	0.20		0.25						
D		3.50 BS							
D2	1.95	2.15	2.05						
Е	с.,	3.50 BS	SC						
E2	1.95	2.15	2.05						
е).50 BS							
e1		1.50 BS	SC						
L			0.40						
k	0	.325 R	EF						
aaa		0.1							
bbb		0.1							
CCC		0.1							
ddd	0.05								
eee		0.08							
fff		0.1							
All	Dimens	sions i	n mm						



Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(3) TSSOP-14

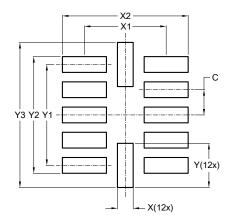


TSSOP-14		
Dim	Min	Max
a1	7° (4X)	
a2	0°	8°
Α	4.9	5.10
В	4.30	4.50
С	-	1.2
D	0.8	1.05
F	1.00 Typ	
F1	0.45	0.75
G	0.65 Typ	
Κ	0.19	0.30
L	6.40 Typ	
All Dimensions in mm		

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) U-QFN1720-12 (Type CJ)



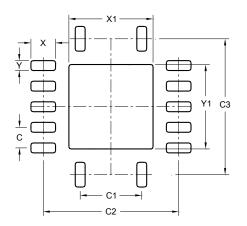
Dimensions	Value (in mm)
С	0.400
Х	0.250
X1	1.300
X2	2.000
Y	0.700
Y1	1.600
Y2	1.850
Y3	2.300



Suggested Pad Layout (continued)

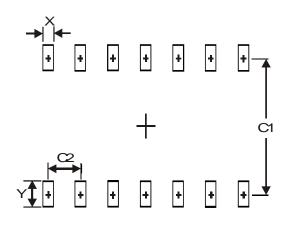
Please see http://www.diodes.com/package-outlines.html for the latest version.

(2) V-QFN3535-14 (Type CJ)



Dimensions	Value (in mm)
С	0.500
C1	1.500
C2	3.300
C3	3.300
Х	0.600
X1	2.050
Ŷ	0.240
Y1	2.050

(3) TSSOP-14



Dimensions	Value (in mm)
Х	0.45
Y	1.45
C1	5.9
C2	0.65

Mechanical Data

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Max Soldering Temperature +260°C for 30 secs as per JEDEC J-STD-020
- Weight:
 - U-QFN1720-12 (Type CJ): 21.5mg (Approximate)
 - V-QFN3535-14 (Type CJ): 32.5mg (Approximate)
 - TSSOP-14: 83.5mg (Approximate)



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